GERMANIUM DIODE

VOLTAGE RANGE: 45 V
CURRENT: 0.1 A

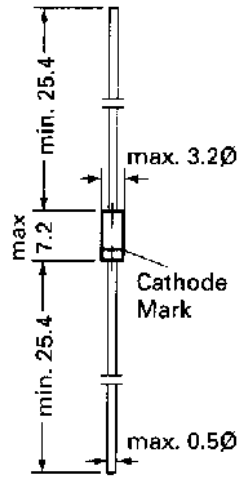
FEATURES

- ◇ Metal sillicon junction majority carrier conduction
- ◇ High current capability,Low forward voltage drop
- ◇ Extremely low reverse current I_R
- ◇ Ultra speed switching characteristics
- ◇ Small temperature coefficient of forward characteristics
- ◇ Satisfactory wave detection efficiency
- ◇ For use in RECORDER. TV. RADIO. TELEPHONE as detectors,super high speed switching circuits, small current rectifier

MECHANICAL DATA

- ◇ Case:JEDEC DO--7 ,glass case
- ◇ Polarity: Color band denotes cathode end
- ◇ Weight: Approx. 0.13 gram

DO - 7 (GLASS)



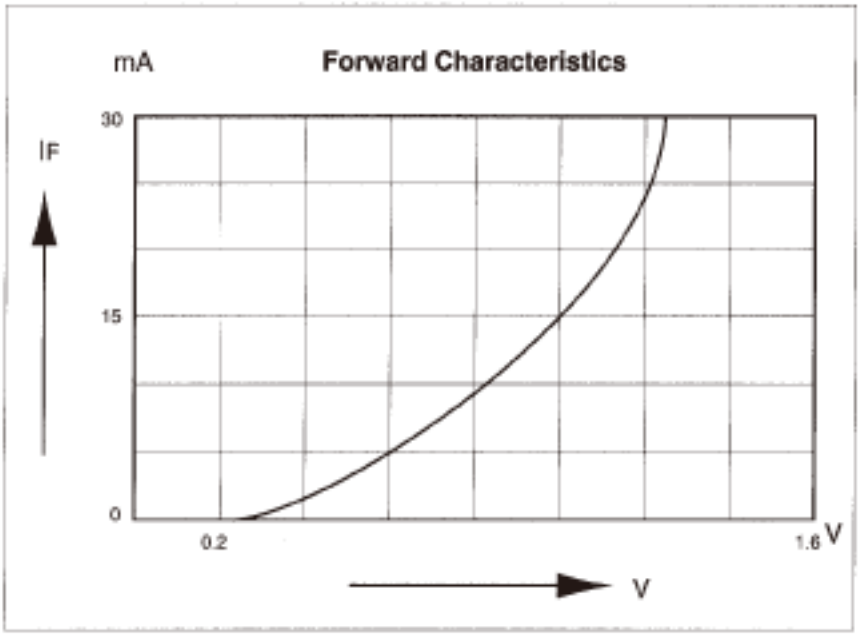
Absolute Maximum Ratings (T_a= 25 °C)

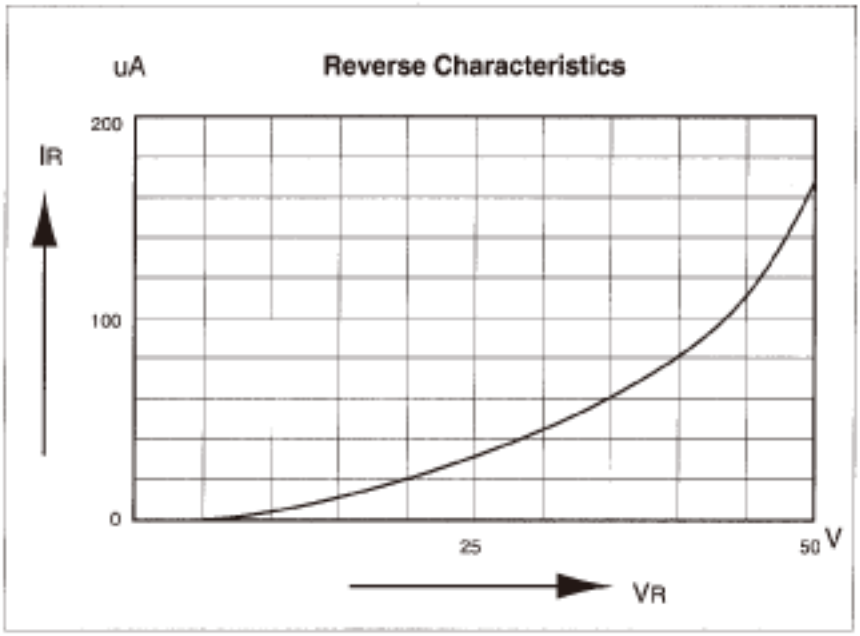
	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage dc	V_R	20	V
Peak Forward Current	I_{FM}	150	mA
Average Rectified Output Current	I_O	50	mA
Surge Forward Current	I_{surge}	500	mA
Junction Temperature	T_j	75	°C
Storage Temperature Range	T_S	-55 to + 75	°C

Characteristics (IN 60 P)

		Symbol	Test condition (T_a 25 ± 2 °C)	Min.	Typ.	Max.	Units
Forward Current		I_F	V_F =1V	4	-	-	mA
Reverse Currents	1N 60P	I_R	V_R = 10V	-	-	50	μA
	1N 60S	I_R	-	-	-	100	μA
Junction Capacitance C		-	f = 1MHz,V = -1V	-	-	1	PF
Rectification efficiency		η	Vi = 2Vrms, =5KΩ C = 20PF, f = 40 MHz	55	-	-	%

Pair $\Delta I_F \leq 6$ mA at 1V, $\Delta I_R \leq 20$ μA at 10V


mA
Forward Characteristics
IF
30
15
0
0.2
1.6
V
V


uA
Reverse Characteristics
IR
200
100
0
25
50
V
VR